

FDC2512

N-Channel PowerTrench® MOSFET 150V 1.4A, 425mΩ

Product Overview

For complete documentation, see the data sheet.

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low RDS(ON) and fast switching speed.

Features

- 1.4 A, 150 V
- RDS(on) = 425 mΩ @ VGS = 10 V
- RDS(on) = 475 mΩ @ VGS = 6 V
- High performance trench technology for extremely low RDS(ON)
- Low gate charge (8nC typical)
- High power and current handling capability
- Fast switching speed

Applications

- This product is general usage and suitable for many different applications.

Part Electrical Specifications																	
Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	V _{DS(BR) Min} (V)	V _{GS Max} (V)	V _{GS(th) Max} (V)	I _{D Max} (A)	P _{D Max} (W)	R _{DS(on) Max @ VGS = 2.5 V} (mΩ)	R _{DS(on) Max @ VGS = 4.5 V} (mΩ)	R _{DS(on) Max @ VGS = 10 V} (mΩ)	Q _{g Typ @ VGS = 4.5 V} (nC)	Q _{g Typ @ VGS = 10 V} (nC)	C _{iss Typ} (pF)	Package Type
FDC2512	0.3125		Active	N-Channel	Single	150	±20	4	1.4	1.6	-	-	425	-	8	344	TSO T-23-6